

b) spraying a silicon source material and hydrogen peroxide (H_2O_2) in a gaseous state on the active matrix at a temperature ranging from approximately $-20\text{ }^{\circ}\text{C}$ to approximately $600\text{ }^{\circ}\text{C}$; and

c) forming the interlayer dielectric layer on the active matrix by a condensation reaction of the silicon source material and the H_2O_2 without performing a post thermal treatment,

wherein the silicon source material includes a tetra-ethyl-ortho-silicate (TEOS).

3. (Amended) The method as recited in claim 2, wherein the tetra-ethyl-ortho-silicate is a modified tetra-ethyl-ortho-silicate (TEOS).

4. (Amended) The method as recited in claim 2, wherein the step of spraying a silicon source material includes supplying simultaneously an inert gas when the silicon source material and the hydrogen peroxide (H_2O_2) are supplied into a flow rate controller.

5. (Amended) The method as recited in claim 2, wherein the step of spraying a silicon source material includes supplying simultaneously an inert gas when the silicon source material and the hydrogen peroxide (H_2O_2) are supplied into a distributor in the chamber.

7. (Twice Amended) The method as recited in claim 2, wherein a pressure in the chamber ranges from approximately 1 Torr to approximately 2 Torr.

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